

Jiangsu WeiDa Semiconductor Co., Ltd.

MBRS10100L 10A High Voltage Power Schottky Rectifier

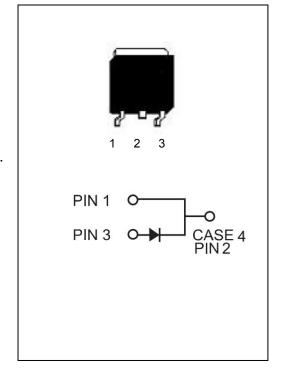
General Description

High voltage dual Schottky rectifier suited for switch mode power supplies and other power converters.

This device is intended for use in medium voltage operation, and particularly, in high frequency circuits where low switching losses and low noise are required.

Main Product Characteristics

symbol	value	unit
I _{F(AV)}	10	Α
V _{RRM}	100	V
V _F	≤0.85	V
TJ	150	$^{\circ}$ C



Features

- High Surge Capacity
- 150°C Operating Junction Temperature
- 10A Total
- Low V_F
- Guard-ring for Stress Protection
- Pb-free Packages are Available

Absolute Maximum Ratings (Per Diode Leg)

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-55~150	$^{\circ}$
Operating junction temperature range	Tj	150	$^{\circ}\!$
Repetitive peak reverse voltage (T _j =25℃)	V_{RRM}	100	V
Maximum RMS voltage	V _{RMS}	70	V
DC Blocking Voltage	V _R	100	V
Average Rectified Forward Current(Rated V _R) T _C =142°C	I _{F(AV)}	10	А

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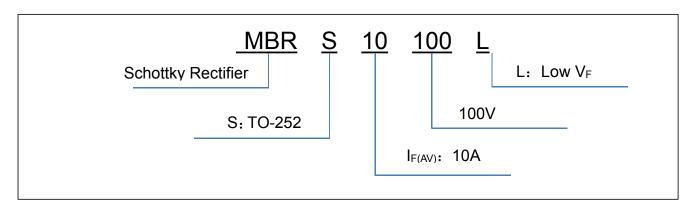
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Peak Repetitive Forward Current (Rated V _R , Square Wave, 20kHz) T _C =142℃	I _{FRM}	10	Α
Non Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Half Wave, Single Phase, 60Hz)	I _{FSM}	120	А
Voltage Rate of Change (Rated V _R)	dv/dt	10000	V/µs

Electrical Characteristics (T_j =25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Value (Max)	Unit
Maximum Instantaneous Forward Voltage Drop	V _F	I _F =10A	0.85	V
Maximum Instantaneous Reverse Current Drop	I _R	V _R =105V	5	μА

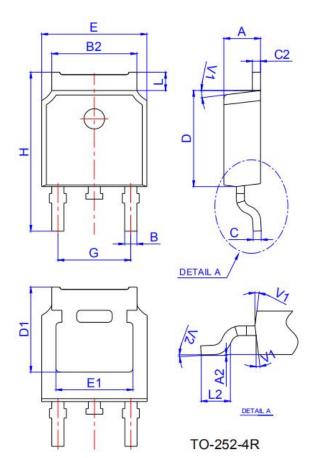
Ordering Information





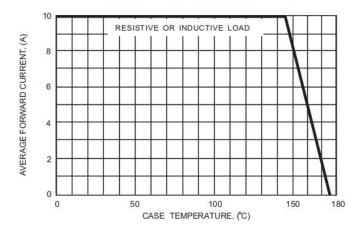
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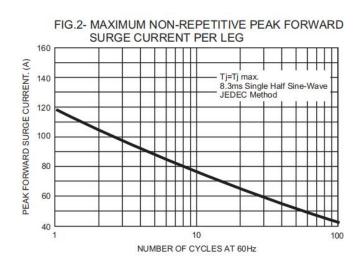
Package Mechanical Data



	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
В	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
С	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252 0.268		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
Н	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

FIG.1- FORWARD CURRENT DERATING CURVE

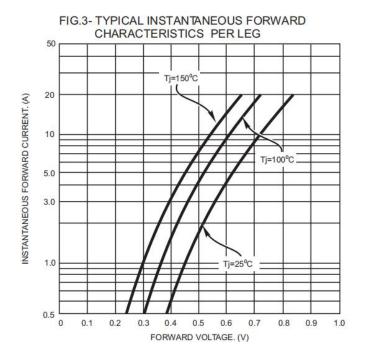


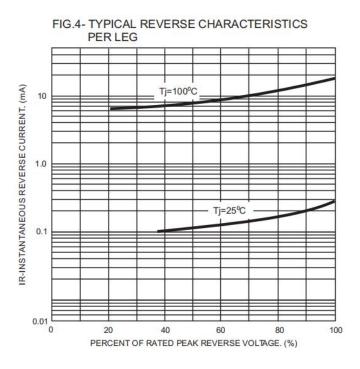


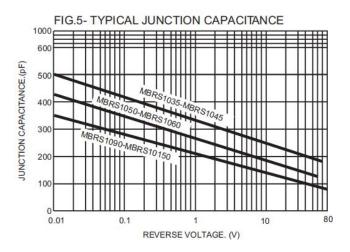


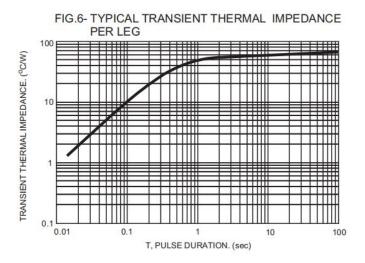
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